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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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Silicon Controlled Rectifiers

Reverse Blocking Thyristors

Designed primarily for half-wave ac control applications, such as motor controls, heating controls, and power supplies; or wherever half-wave, silicon gate-controlled devices are needed.

Features

- Blocking Voltage to 800 Volts
- On-State Current Rating of 16 Amperes RMS
- High Surge Current Capability 160 Amperes
- Rugged Economical TO-220AB Package
- Glass Passivated Junctions for Reliability and Uniformity
- Minimum and Maximum Values of I_{GT}, V_{GT}, and I_H Specified for Ease of Design
- High Immunity to dv/dt 100 V/µsec Minimum at 125°C
- These are Pb-Free Devices

MAXIMUM RATINGS (T.I = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off–State Voltage (Note 1) (T _J = -40 to 125°C, Sine Wave, 50 to 60 Hz, Gate Open) MCR16NG	V _{DRM,} V _{RRM}	800	V
On-State RMS Current (180° Conduction Angles; T _C = 80°C)	I _{T(RMS)}	16	Α
Peak Non-repetitive Surge Current (1/2 Cycle, Sine Wave 60 Hz, T _J = 125°C)	I _{TSM}	160	Α
Circuit Fusing Consideration (t = 8.3 ms)	I ² t	106	A ² sec
Forward Peak Gate Power (Pulse Width \leq 1.0 μ s, T _C = 80°C)	P _{GM}	5.0	W
Forward Average Gate Power (t = 8.3 ms, T _C = 80°C)	P _{G(AV)}	0.5	W
Forward Peak Gate Current (Pulse Width $\leq 1.0 \ \mu s, T_C = 80^{\circ}C$)	I _{GM}	2.0	Α
Operating Junction Temperature Range	TJ	-40 to +125	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

 V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

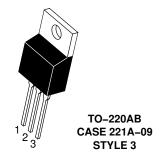
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Littelfuse.com

SCRs 16 AMPERES RMS 800 VOLTS









= Assembly Location

Y = Year
WW = Work Week
G = Pb-Free Package
AKA = Diode Polarity

PIN ASSIGNMENT			
1	Cathode		
2	Anode		
3	Gate		
4	Anode		

ORDERING INFORMATION

Device	Device Package S		
MCR16NG	TO-220AB (Pb-Free)	50 Units / Rail	

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case Junction-to-Ambient	$R_{ hetaJC} \ R_{ hetaJA}$	1.5 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	TL	260	°C

ELECTRICAL CHARACTERISTICS (T₁ = 25°C unless otherwise noted)

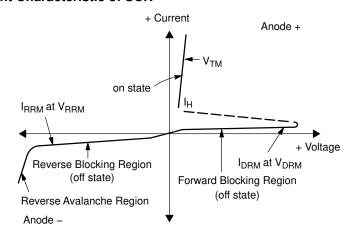
Characteristic			Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Peak Repetitive Forward or Reverse Blocking Current $(V_{AK} = Rated V_{DRM} \text{ or } V_{RRM}, \text{ Gate Open})$	$T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$	I _{DRM} , I _{RRM}	_ _	- -	0.01 2.0	mA
ON CHARACTERISTICS						
Peak Forward On–State Voltage (Note 2) (I _{TM} = 32 A)		V _{TM}	_	-	1.7	V
Gate Trigger Current (Continuous dc) $(V_D = 12 \text{ V}, R_L = 100 \Omega)$		I _{GT}	2.0	10	20	mA
Gate Trigger Voltage (Continuous dc) $ (V_D = 12 \ V, \ R_L = 100 \ \Omega) $		V _{GT}	0.5	0.65	1.0	V
Hold Current (Anode Voltage = 12 V, Initiating Current = 200 mA, Gate Open)		I _H	4.0	25	40	mA
Latch Current (V _D = 12 V, Ig = 200 mA)		ΙL	-	30	60	mA
DYNAMIC CHARACTERISTICS						
Critical Rate of Rise of Off–State Voltage (V _D = Rated V _{DRM} , Exponential Waveform, Gate Open, T _J = 125°C)	1	dv/dt	100	300	-	V/μs
Critical Rate of Rise of On–State Current (I _{PK} = 50 A, Pw = 30 µs, diG/dt = 1 A/µsec, Igt = 50 mA)		di/dt	-	-	50	A/μs

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Indicates Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle $\leq 2\%$.

Voltage Current Characteristic of SCR

Symbol	Parameter
V _{DRM}	Peak Repetitive Off State Forward Voltage
I _{DRM}	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Off State Reverse Voltage
I _{RRM}	Peak Reverse Blocking Current
V_{TM}	Peak On State Voltage
I _H	Holding Current



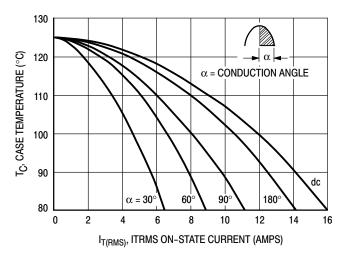


Figure 1. Typical RMS Current Derating

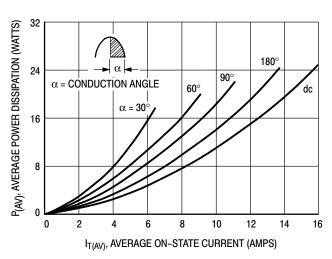


Figure 2. On State Power Dissipation

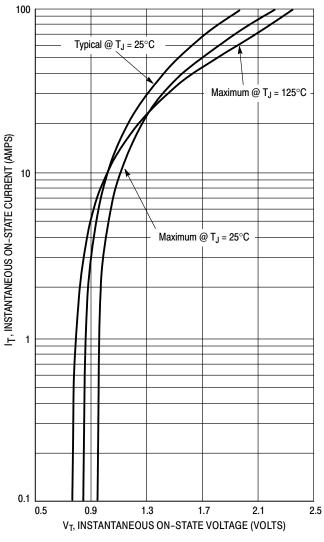


Figure 3. Typical On-State Characteristics

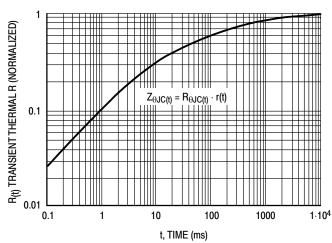


Figure 4. Transient Thermal Response

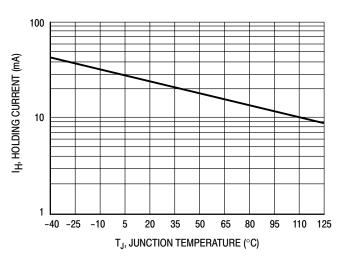


Figure 5. Typical Holding Current versus Junction Temperature

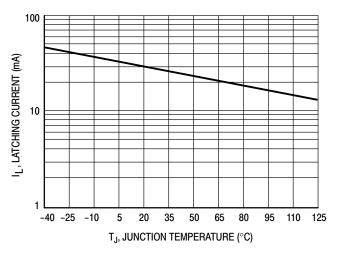


Figure 6. Typical Latching Current versus Junction Temperature

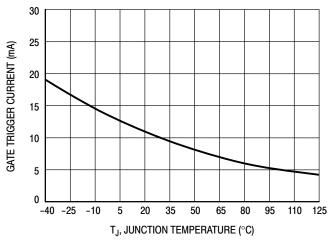


Figure 7. Typical Gate Trigger Current versus Junction Temperature

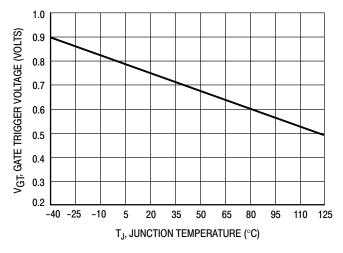


Figure 8. Typical Gate Trigger Voltage versus Junction Temperature

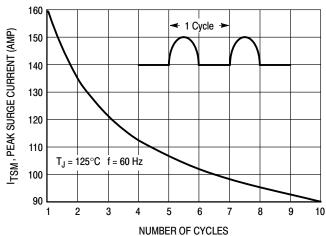
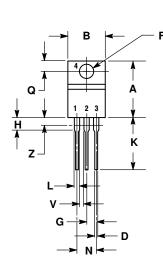
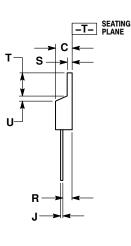


Figure 9. Maximum Non-Repetitive Surge Current

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AH**





- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
- DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

STYLE 3:

PIN 1. CATHODE

- 2. ANODE
- GATE
- ANODE

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